

Product Summary

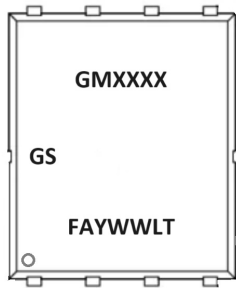
V_{DS} (V)	$R_{DS(on),max}$ (mΩ)	I_D (A)
30	0.7 @ $V_{GS} = 10V$	330 ⁽¹⁾

Features

- Low $R_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Application

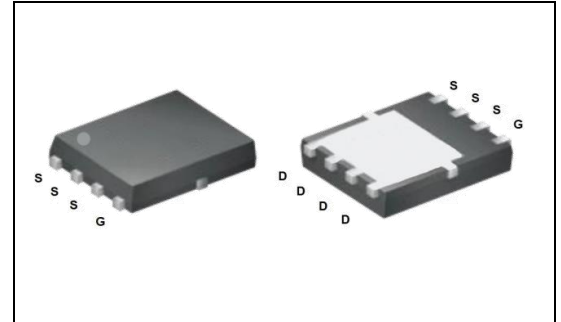
- DC/DC conversion
- Power switch
- Motor drives
- Li- Battery Protection



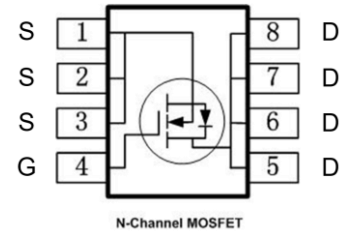
PDFN5X6

NOTE:
 LOGO - GS
 GMXXXXX- Part number code
 F - Fab location code
 A - Assembly location code
 Y - Year code
 WW - Week code
 L&T - Assembly lot code

PDFN5X6



Equivalent circuit



Absolute maximum rating@25°C

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GS}	±20	
Continuous drain current	I_D	330	A
	I_D	209	
Pulsed drain current ⁽²⁾	$I_{D,pulse}$	1319	
Avalanche energy, single pulse ⁽³⁾	E_{AS}	960	mJ
Power dissipation	P_D	114	W
	P_D	45	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to 150	°C

Thermal Characteristic

Parameter	Symbol	Max.	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	1.1	°C/W
Thermal resistance, junction-to-ambient ⁽⁴⁾	$R_{\theta JA}$	43	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Static parameter						
Drain to source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0, I _D = 250 μA	30			V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2	1.4	2.5	V
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.57	0.7	mΩ
				0.87	1.0	mΩ
Forward transconductance ⁽⁵⁾	g _{fs}	V _{DS} = 5 V, I _D = 20 A		69		S
Gate resistance	R _g	f = 1 MHz		2.0		Ω
Dynamic ⁽⁵⁾						
Total gate charge V _{GS} = 10V	Q _g	V _{DS} = 15 V, I _D = 20 A, V _{GS} = 10 V		114		nC
Total gate charge V _{GS} = 4.5V	Q _g			57		
Gate-source charge	Q _{gs}			15.5		
Gate-drain charge	Q _{gd}			22		
Turn-on delay time	t _{d(on)}	V _{DS} = 15 V, I _D = 20 A, V _{GS} = 10 V, R _{GEN} = 3 Ω		5.7		ns
Rise time	t _r			13.8		
Turn-off delay time	t _{d(off)}			95		
Fall time	t _f			47		
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		6370		pF
Output capacitance	C _{oss}			3760		
Reverse transfer capacitance	C _{rss}			475		
Reverse Diode Characteristics ⁽⁵⁾						
Diode forward voltage	V _{SD}	V _{GS} = 0 V, I _F = 2 A		0.7	1.2	V
Reverse recovery time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		66		ns
Reverse recovery charge	Q _{rr}			87		nC

Notes

- (1) Limited by maximum junction temperature.
- (2) Pulse width limited by maximum junction temperature.
- (3) V_{DS} = 15 V, V_{GS} = 10 V, L = 1.0 mH.
- (4) Device mounted on FR-4 substrate PC board with 2oz copper in 1inch square cooling area.
- (5) Guaranteed by design, not subject to production testing.

Typical Performance Characteristics

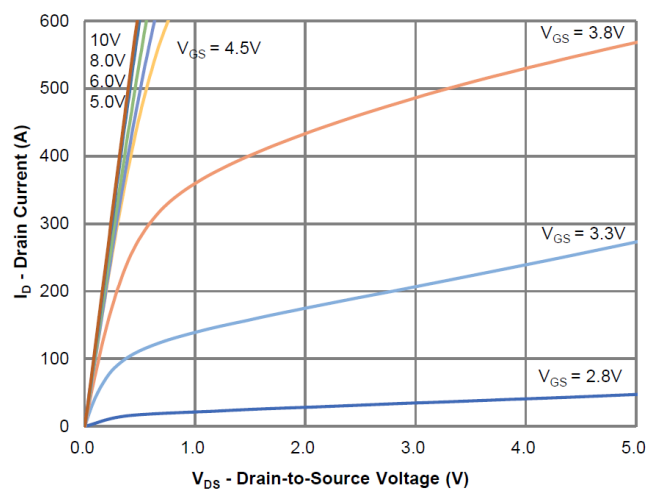


Figure 1: Output Characteristics

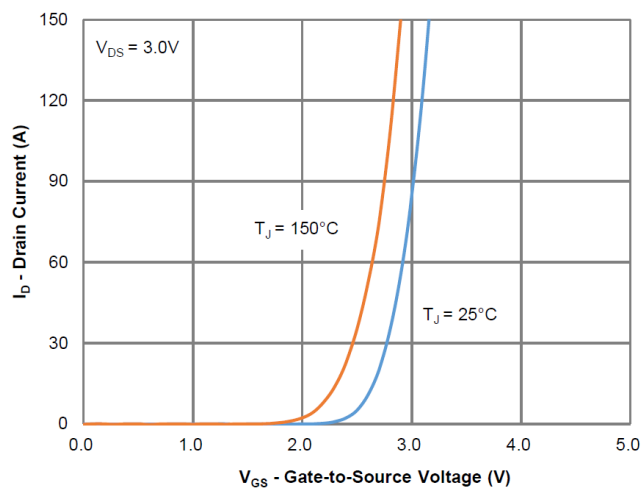


Figure 2: Transfer Characteristics

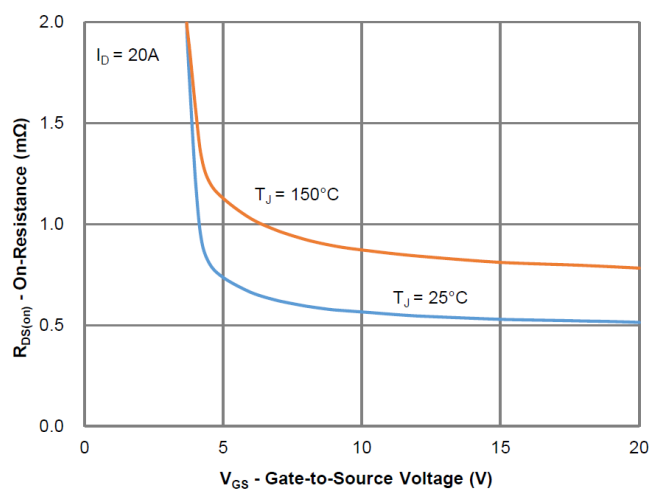


Figure 3: On-Resistance vs. Gate-Source Voltage

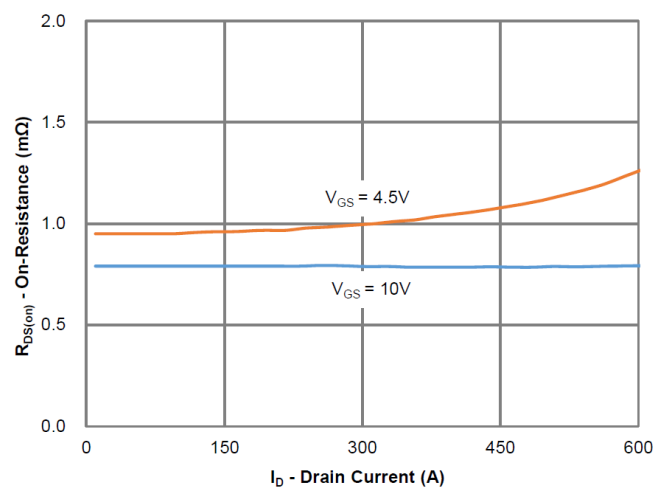


Figure 4: On-Resistance vs. Gate-Source Voltage

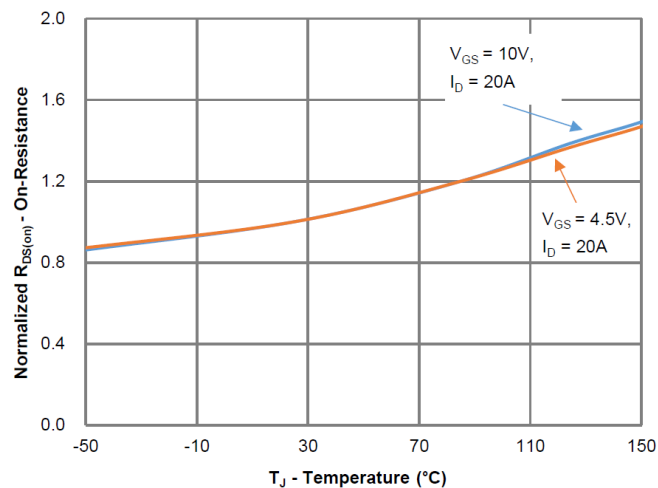


Figure 5: On-Resistance vs. Junction Temperature

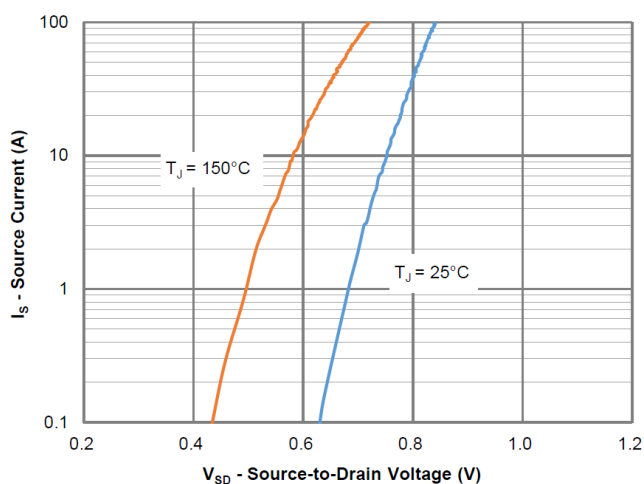


Figure 6: Source-Drain Diode Forward Voltage

Typical Performance Characteristics

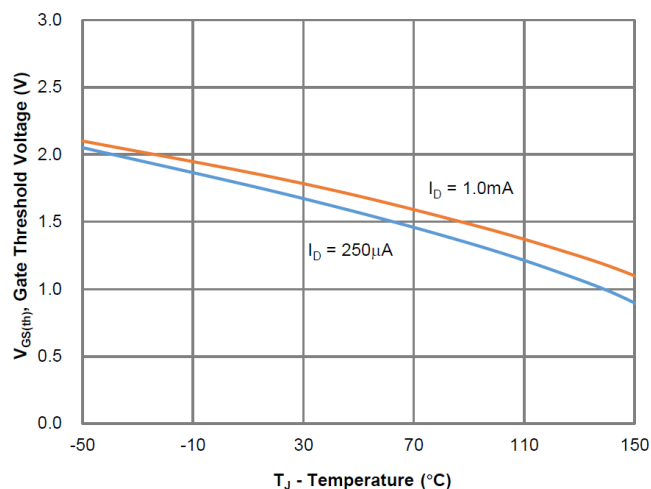


Figure 7: Gate Threshold Variation vs. Junction Temperature

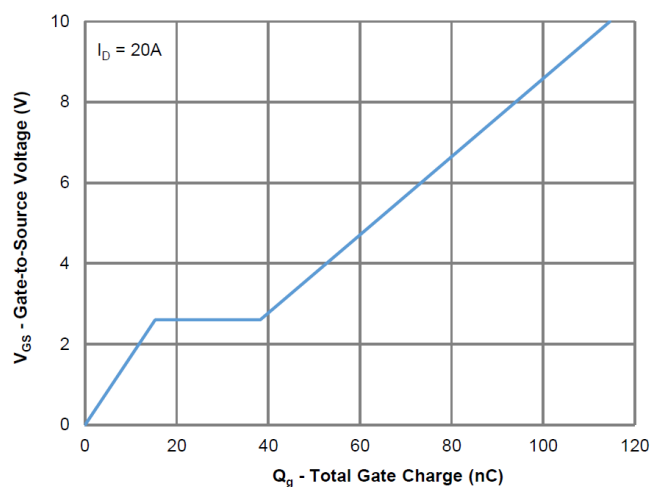


Figure 8: Gate Charge Characteristics

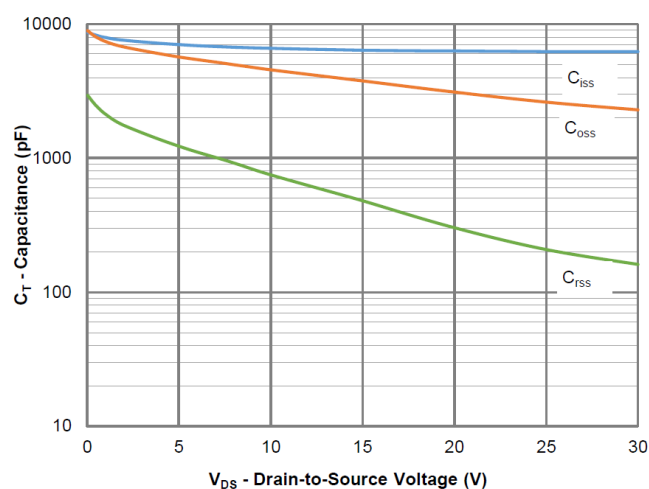


Figure 9: Capacitance Characteristics

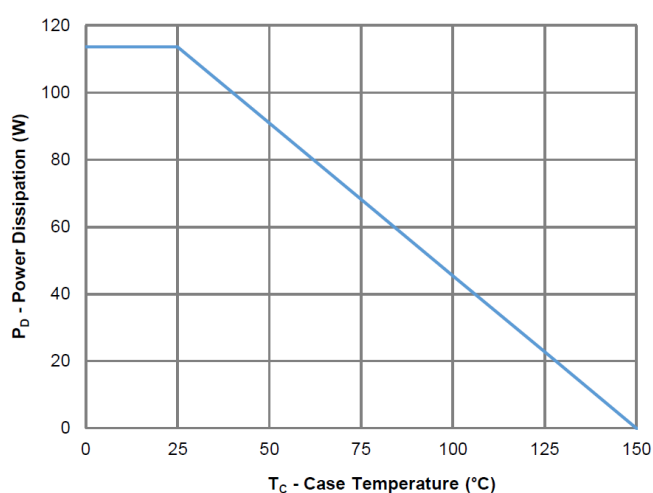


Figure 10: Power Derating

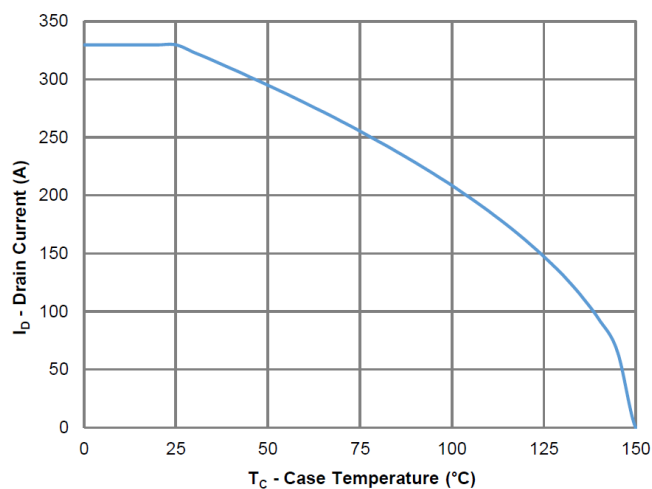


Figure 11: Current Derating

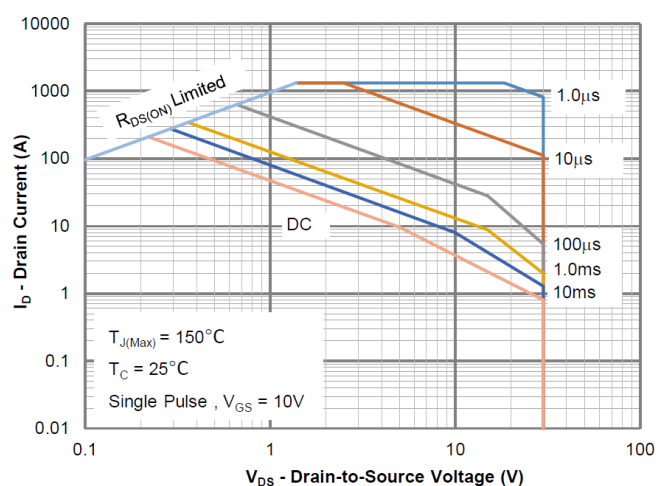


Figure 12: Safe Operating Area

Typical Performance Characteristics

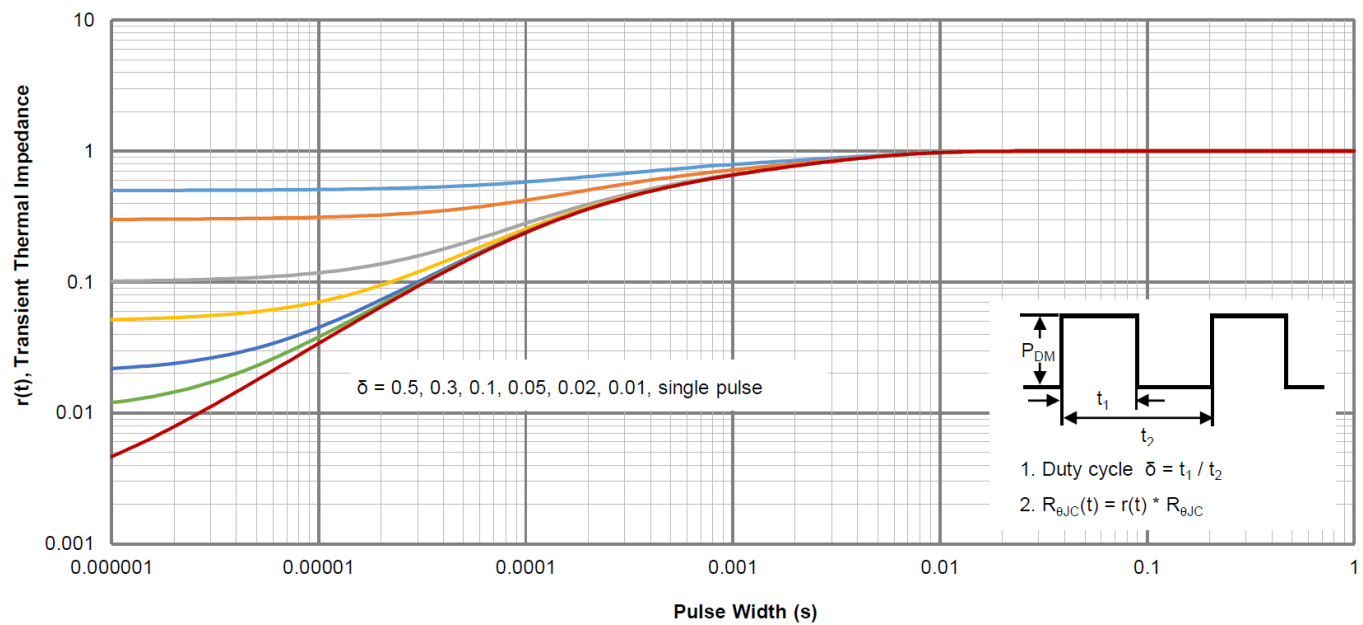
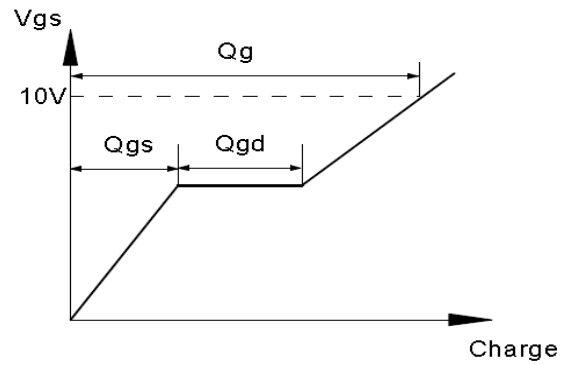
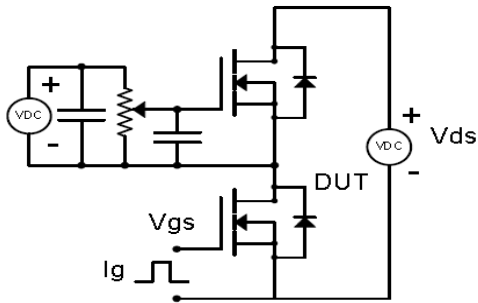


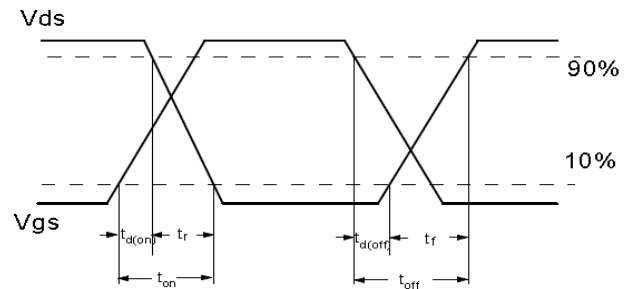
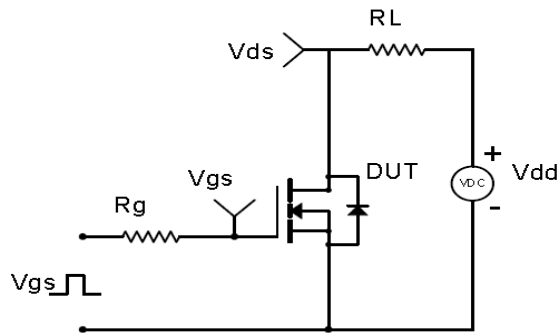
Figure 13: Normalized Maximum Transient Thermal Impedance

Test Circuit & Waveform

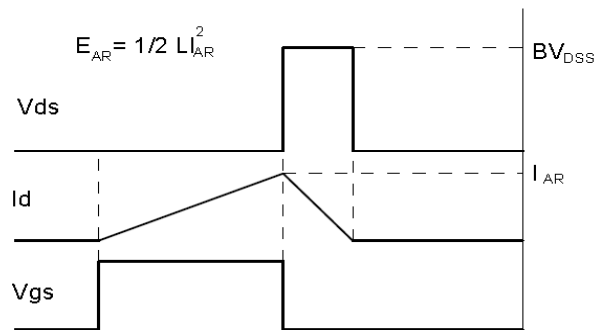
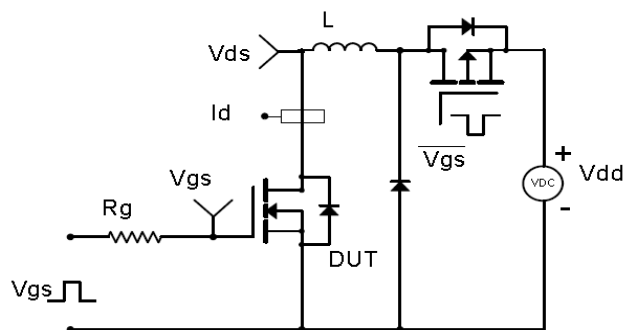
Gate Charge Test Circuit & Waveform



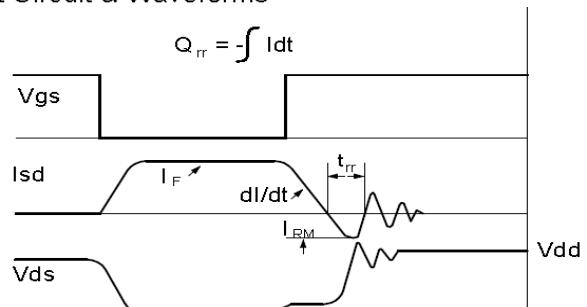
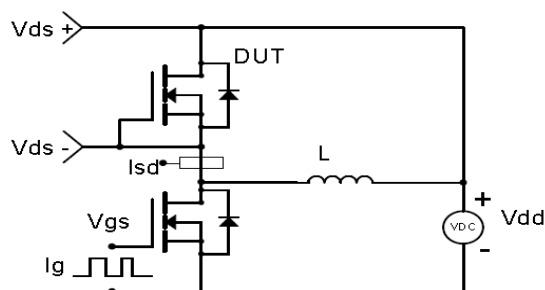
Resistive Switching Test Circuit & Waveforms

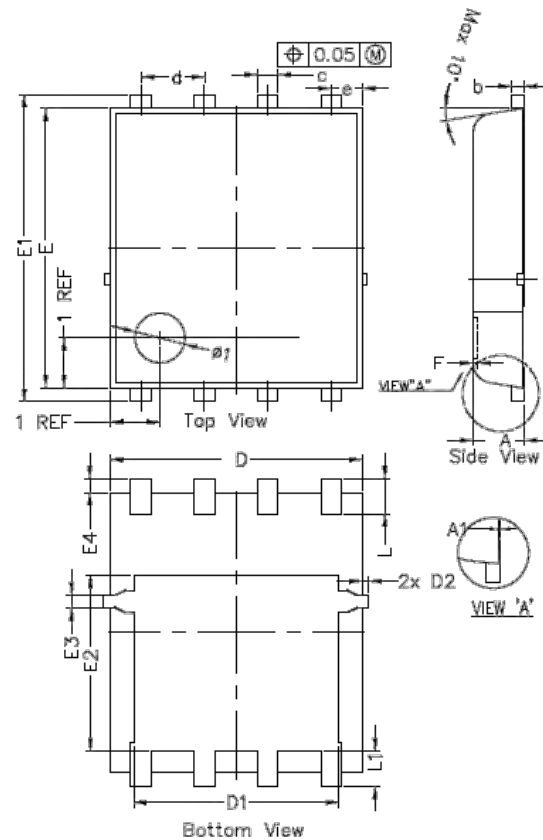


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Outline Drawing PDFN5X6


Dim	Millimeters		
	Min	Nom	Max
A	0.900	1.000	1.100
A1	0.000	---	0.050
b	0.246	0.254	0.312
c	0.310	0.410	0.510
d	1.27BSC		
D	4.950	5.050	5.150
D1	4.000	4.100	4.200
D2	---	---	0.125
e	0.62BSC		
E	5.500	5.600	5.700
E1	6.050	6.150	6.250
E2	3.425	3.525	3.625
E3	0.150	0.250	0.350
E4	0.175	0.275	0.375
F	---	---	0.100
L	0.500	0.600	0.700
L1	0.600	0.700	0.800

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